

# 2SC5209-TH51

FOR RELAY DRIVE POWER SUPPLY APPLICATION  
SILICON NPN EPITAXIAL TYPE

AEC-Q101 Compliance

## DESCRIPTION

2SC5209 is a silicon NPN epitaxial type transistor. It designed with high voltage, high collector current and high hFE.

Complementary with 2SA1944.

## FEATURE

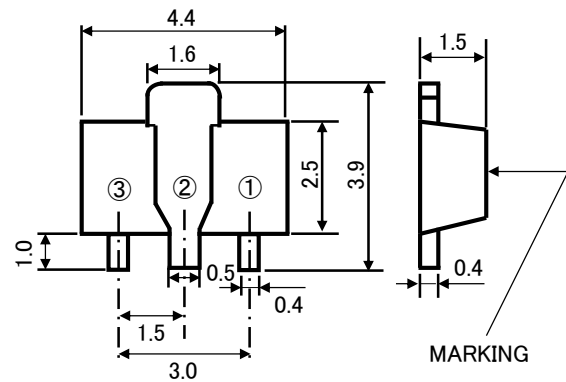
- Small package for mounting.
- High hFE hFE=600~1800
- Small collector to emitter saturation voltage.  
VCE(sat)=0.15V typ (@IC=500mA, IB=10mA)
- High voltage VCEO=50V

## APPLICATION

Audio machine, VTR, relay drive of other electronic machine, power supply.

## OUTLINE DRAWING

UNIT:mm



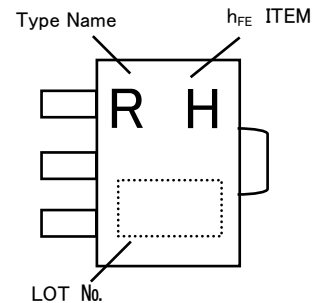
### TERMINAL CONNECTOR

- ①: BASE JEITA: SC-62
- ②: COLLECTOR JEDEC: SOT-89
- ③: EMITTER

## MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CBO</sub>	Collector to Base voltage	50	V
V <sub>EBO</sub>	Emitter to Base voltage	6	V
V <sub>CEO</sub>	Collector to Emitter voltage	50	V
I <sub>C</sub>	Collector current	1	A
I <sub>CM</sub>	Peak collector current	2	A
P <sub>C</sub>	Collector dissipation(Ta=25°C)	500	mW
T <sub>j</sub>	Junction temperature	+150	°C
T <sub>stg</sub>	Storage temperature	-55~+150	°C

## MARKING



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
V <sub>(BR)CBO</sub>	C to B breakdown voltage	I <sub>C</sub> =10 μA, I <sub>E</sub> =0mA	50	-	-	V
V <sub>(BR)EBO</sub>	E to B breakdown voltage	I <sub>E</sub> =10 μA, I <sub>C</sub> =0mA	6	-	-	V
V <sub>(BR)CEO</sub>	C to E breakdown voltage	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	50	-	-	V
I <sub>CBO</sub>	Collector cut off current	V <sub>CB</sub> =40V, I <sub>E</sub> =0mA	-	-	0.1	μA
I <sub>EBO</sub>	Emitter cut off current	V <sub>EB</sub> =2V, I <sub>C</sub> =0mA	-	-	0.1	μA
hFE ※	DC forward current gain	V <sub>CE</sub> =6V, I <sub>C</sub> =100mA	600	-	1800	-
V <sub>CE(sat)</sub>	C to E saturation voltage	I <sub>C</sub> =500mA, I <sub>B</sub> =10mA	-	0.15	0.5	V
fT	Gain bandwidth product	V <sub>CE</sub> =10V, I <sub>E</sub> =-10mA	-	130	-	MHz
Cob	Collector output capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0mA, f=1MHz	-	12	-	pF

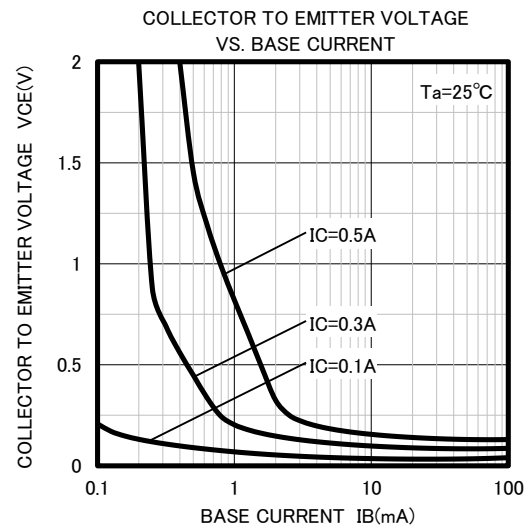
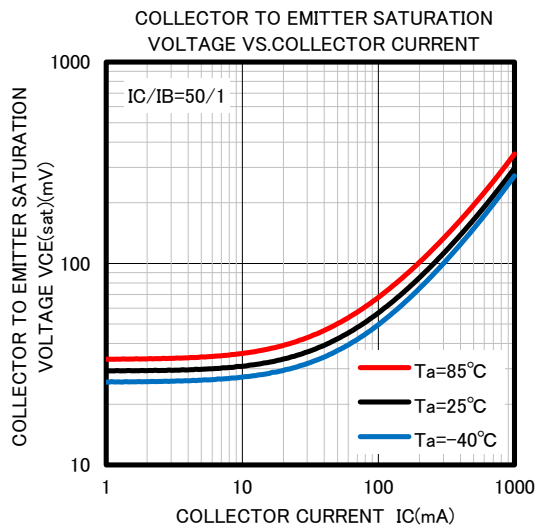
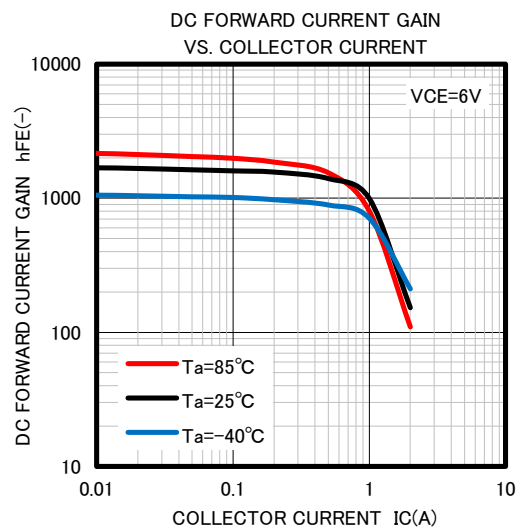
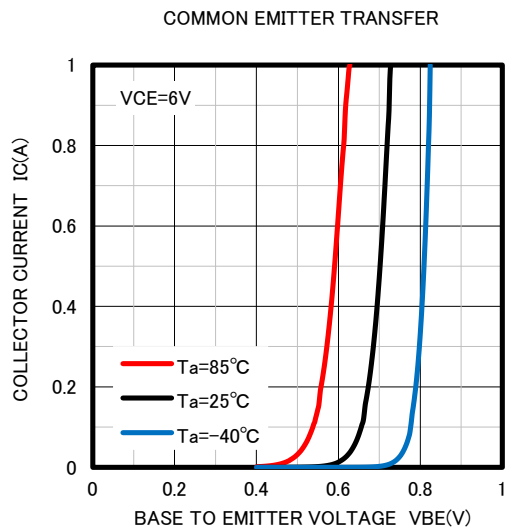
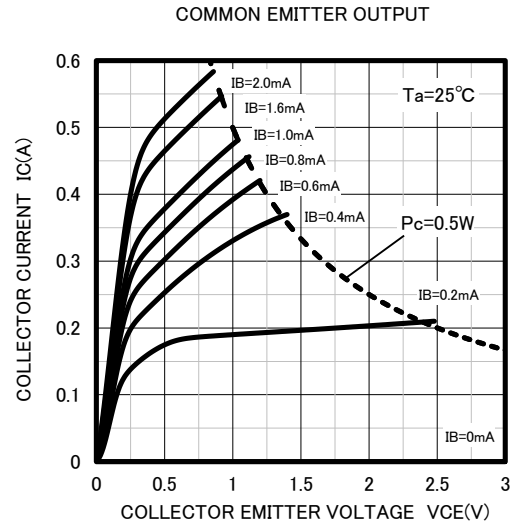
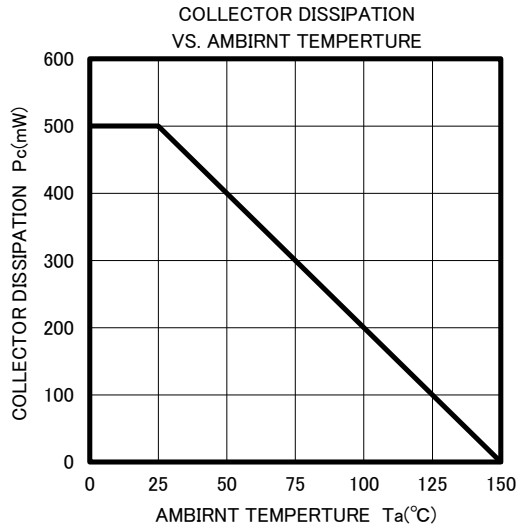
※) It shows hFE classification at right table.

Item	H	J
hFE	600~1200	900~1800

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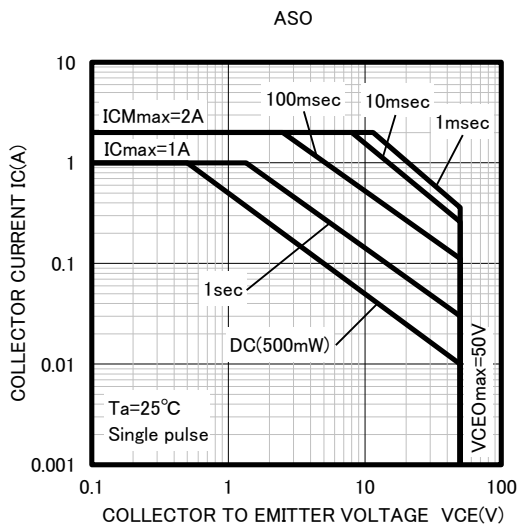
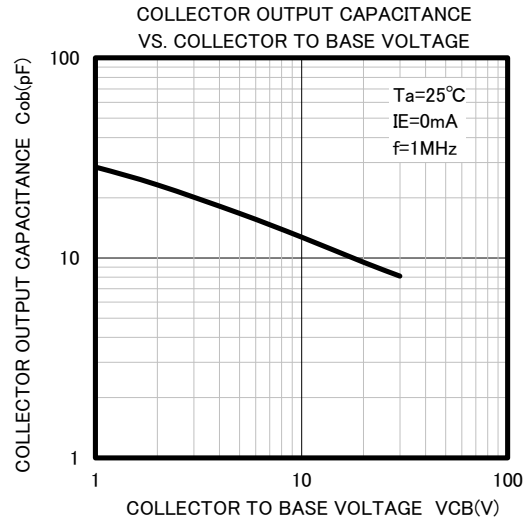
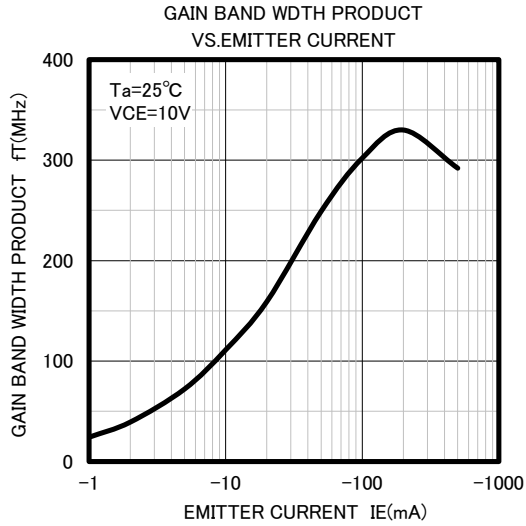
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## TYPICAL CHARACTERISTICS



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